PCN Number:		2018	307120	PCN Date: Jul 16, 2018				ul 16, 2018						
Title:	Title: Qualification of DMOS6 as an additional Fab site and Assembly material change at UTL1 for select devices													
Customer Contact:				PCN Manager D			De	Dept:		Qu	ality Services			
Propose	d 1 st Sh	ip Date	:	Cct 16, 2018				Estimate Availabil		mpl	e	-	te Provided at mple request	
Change '	Гуре:													
Asse	mbly Sit	e					Desig	n				Wafer	Bu	mp Site
	mbly Pro	cess		Data S			Shee				Wafer	Wafer Bump Material		
	mbly Ma				Part number change							mp Process		
	anical S					=	Test S				Wafer Fab Site			
	ng/Ship	ping/La	beling]	Test Process Wafer Fab Materials									
								De	taile			water	Fat	b Process
Descript			-				PCN	De	talis					
Descript		nange												
	materia	Il chang	e at I	UTL1 f					of DMOS6 5. Material	diffe	renc	es as fo	ollo	ws.
	Cι	irrent l	ab S	Site						Add	itior	nal Fab	Sit	te
Curren Sit		Proc	ess			/afe me	er eter		New Fab Site		Pro	ocess		Wafer Diameter
DP1D	M5	LBC	8LV		20)0m	nm		DMOS6		LB	C8LV		300mm
Material change: Fro Mount compound PZ00 Mold compound CZ01			037	7			To PZ0076 CZ0288							
Reason f	or Char	nge:												
Continuit		_												
	<u> </u>	· .	Form	. Eit	E	unci	tion	0	lity or Pol	iahili		nocitiv	10	negative):
-	teu imp		FUIII	I, FIL,	ги		tion,	Qua	ity of Kei	Iavii	ity (positiv	/e /	negative):
None														
Anticipa											<u> </u>	•		
Material Declaration pro- rel ob ma			Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <u>TI Eco-Info website</u> . There is no impact to the material meeting current regulatory compliance requirements with this PCN change.											
Changes to product identification resulting from this PCN:														
Fab Site change: Current:														
Current Chip Site Chip Site Origin		n Code (20L)		Chip Site Country Co		v Code (21L) Chin Site		Chip Site City						
DP1DM5 DM5				USA				· · · ·						
New Fab Site:														
		Chir) Site	Origin		ode	(20)		hin Site Co	nuntr		de (21)		Chip Site City
New Chip Site Chip DMOS6			p Site Origin Code (20L) DM6				Chip Site Country Code (21 USA			-/	Dallas			
		I		2110	-					50,	-			_ 0.00

Sample Product Shipping Label (not actual product label)					
MADE IN: Malaysia 2DC: 2Q: MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: 39 LBL: 5A (L)T0:1750 Product Affected:		(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (P) (2P) REV: (V) 0033317 (20L) CS0: SHE (21L) CC0:USA (22L) AS0: MLA (23L) AC0: MYS			

Product Affected:							
TMP451AIDQFR	TMP451CIDQFR	TMP451EIDQFR	TMP451GIDQFR				
TMP451AIDQFT	TMP451CIDQFT	TMP451EIDQFT	TMP451GIDQFT				
TMP451BIDQFR	TMP451DIDQFR	TMP451FIDQFR					
TMP451BIDQFT	TMP451DIDQFT	TMP451FIDQFT					

Qualification Report TMP451 RFAB/DMOS6-UTAC QUALIFICATION

Approve Date: 07/11/2018

Product Attributes

Attributes	Qual Device: <u>TMP451AIDQF</u>	QBS Process Reference: <u>TAS2553YFF</u>				
Assembly Site	UTAC	CLARK-AT				
Package Family	SON	DSBGA				
Flammability Rating	UL 94 V-0	UL 94 V-0				
Wafer Fab Supplier	RFAB / DMOS6 (MFF)	RFAB/DMOS6 (MFF)				
Wafer Process	LBC8LV	LBC8LV				

- QBS: Qual By Similarity

- Qual Device TMP451AIDQF is qualified at LEVEL1-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: <u>TMP451AIDQF</u>	QBS Process Reference: <u>TAS2553YFF</u>
HTOL	High Temp Operating Life	125C 1000 Hours	1/77/0	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	-
HAST	Biased HAST, 110C/85%RH	264 Hours	3/231/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	-
UHAST	Unbiased HAST 110C/85%RH	264 Hours	3/231/0	-
CDM	ESD - CDM	1500 V	1/3/0	-
HBM	ESD - HBM	4000 V	1/3/0	-
LU	Latch-up	(per JESD78)	1/6/0	-
PD	Physical Dimensions	-	3/15/0	-
SD	Surface Mount Solderability (Pb Free)	8 Hours Steam Age	3/66/0	-
SD	Surface Mount Solderability (Pb)	8 Hours Steam Age	3/66/0	-
WBP	Bond Pull	Wires	3/90/0	-
WBS	Ball Bond Shear	Wires	3/90/0	-

Туре	Test Name / Condition	Duration	Qual Device: <u>TMP451AIDQF</u>	QBS Process Reference: <u>TAS2553YFF</u>
ED	Electrical Characterization	Per Datasheet Parameters	1/30/0	-
BLR	BLR-Temp Cycle, -40C/125C	2000 Cycles	1/32/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

THIS INFORMATION RELATING TO QUALITY AND RELIABILITY IS PROVIDED "AS IS." Product information detailed in this report may not accurately reflect TI's current product materials, processes and testing used in the construction of the TI products. Customers are solely responsible to conduct sufficient engineering and additional qualification testing to determine whether a device is suitable for use in their applications. Using TI products outside limits stated in TI's datasheet may void TI's warranty. See TI's Terms of Sale at "http://www.ti.com/lsds/ti/legal/termsofsale.page"

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